# N-Channel 250-V (D-S) MOSFET

#### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- Low thermal impedance
- · Fast switching speed

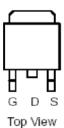
#### **Typical Applications:**

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
Vds (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
250	52 @ V <sub>GS</sub> = 10V	62		
230	56 @ V <sub>GS</sub> = 6.5V	60		

## TO-263





ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)							
Parameter			Limit	Units			
Drain-Source Voltage	Source Voltage						
Gate-Source Voltage		V <sub>GS</sub>	±20	V			
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> =25°C	I <sub>D</sub>	62	А			
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	200	A			
Continuous Source Current (Diode Conduction) <sup>a</sup>	T <sub>C</sub> =25°C	I <sub>S</sub>	62	А			
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	PD	300	W			
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C			

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient °	$R_{ extsf{ heta}JA}$	62.5	°C/W			
Maximum Junction-to-Case	$R_{ extsf{ heta}JC}$	0.5	C/W			

Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature
- c. Surface Mounted on 1" x 1" FR4 Board.

### **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \text{ uA}$	1			V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			±100	nA		
Zero Gate Voltage Drain Current		$V_{DS} = 200 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	1 10		1	uA		
Zero Gale Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 200 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10			
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 V, V_{GS} = 10 V$	85			А		
Droin Course On Desistence a	r	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 30 \text{ A}$			52	mΩ		
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = 6.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		56		mc2		
Forward Transconductance <sup>a</sup>	<b>g</b> <sub>fs</sub>	$V_{DS} = 15 \text{ V}, \text{ I}_{D} = 30 \text{ A}$		33		S		
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{\rm S} = 30$ A, $V_{\rm GS} = 0$ V		0.87		V		
		Dynamic <sup>b</sup>						
Total Gate Charge	$Q_g$	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 6.5 V,		74		nC		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 100 V, V_{GS} = 0.3 V,$ $I_{D} = 30 A$		32				
Gate-Drain Charge	$Q_gd$	10 - 00 / 1		31				
Turn-On Delay Time	t <sub>d(on)</sub>	V 100 V B = 3.3.0		50				
Rise Time	t <sub>r</sub>	$V_{DS} = 100 \text{ V}, \text{ R}_{L} = 3.3 \Omega,$ $I_{D} = 30 \text{ A}.$		50		ns		
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN} = 10 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		108				
Fall Time	t <sub>f</sub>	$V_{\text{GeN}} = 10^{\circ} V$ , $V_{\text{GeN}} = 0.22$		40				
Input Capacitance	C <sub>iss</sub>			5525				
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		409		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>			170				

#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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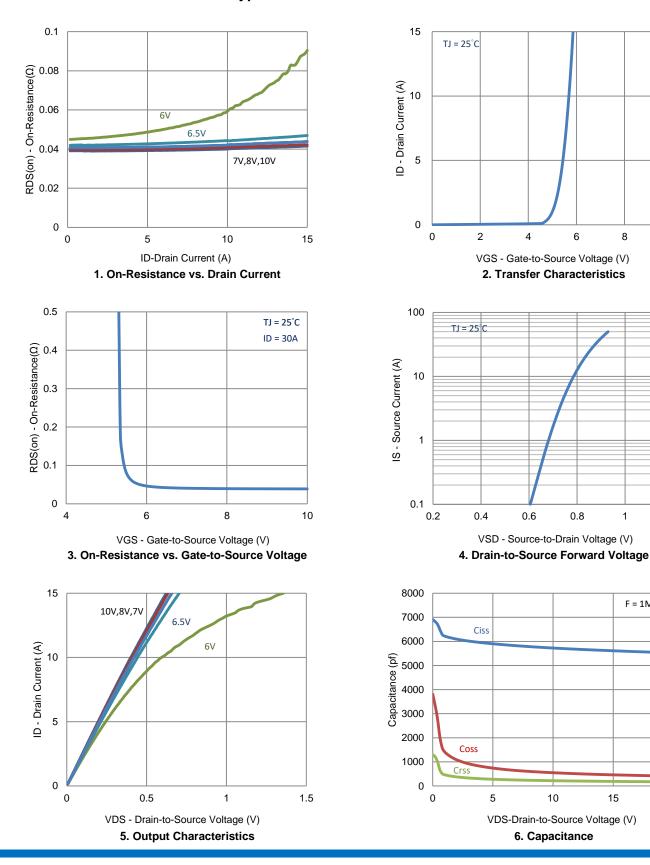
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F = 1MHz

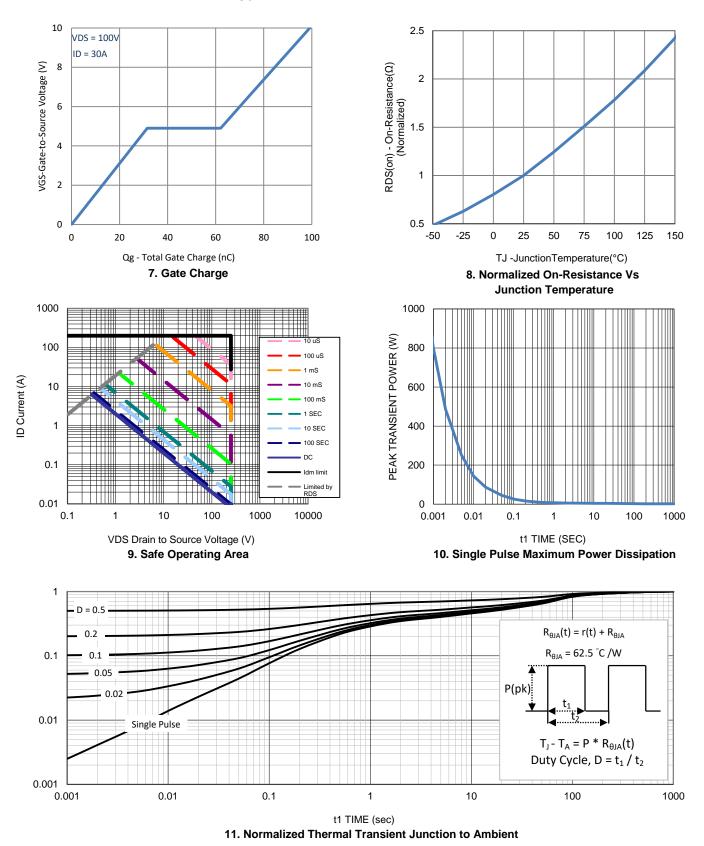
1.2

20

10

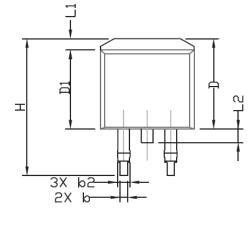


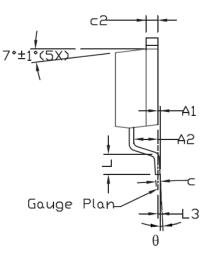
#### **Typical Electrical Characteristics**

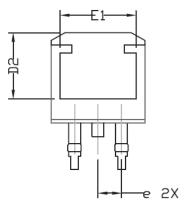


#### **Typical Electrical Characteristics**

## Package Information







0.440	DIMENS:	IONAL F	REQMTS	INCH	ES REG	MTS		
SYMBOL	MIN	NLM	MAX	MĪN	NDM	MAX		
A	4,30	4.57	4,72	0.169	0.180	0.186		
A1	0		0,25	0		0.010		
A2	2,47	2.57	2,67	0.097	0.101	0.105		
b	0.69	0.813	0.94	0.027	0.032	0.037		
b2	1,17	1,27	1,45	0.046	0.050	0.057		
С	0.48	0,50	0.60	0.019	0.020	0.024		
c2	1,17	1.27	1.37	0.046	0.050	0.054		
D	9,80	10.05	10,30	0.386	0,396	0.406		
D1	8,64	8,78	9,65	0.340	0.346	0,380		
D2	7.12	7.37	7,62	0.280	0,290	0.300		
E	9,70	10.15	10.54	0.382	0.400	0.415		
E1	8,00	8,20	8,40	0.315	0,323	0,331		
e	2.54 BSC			0,	0.100 BSC			
Н	14.99	15.24	15,49	0.590	0.600	0.610		
L	1.78	2.29	2,79	0.070	0.090	0.110		
L1	1.02	1.27	1.52	0.040	0.050	0.060		
L2			1.75			0.069		
L3		0.254			0.010			
θ	0°		8*	0°		8*		